ABSTRACT

**ANTIFUSE CELL WITH TUNGSTEN SILICIDE ELECTRODE**

An improved antifuse design has been achieved by using a structure comprising a region of heavily doped N type silicon coated with a layer of ONO (oxide-nitride-oxide). Top contact to the ONO is made through a layer of tungsten silicide sandwiched between two layers of N type polysilicon. A cost effective method for manufacturing said antifuse structure is described.

**(FIGURE 2 IS SUGGESTED FOR PUBLICATION)**